

You Think LDOs are Simple?

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Topics

- Noise
- PSRR
- Thermal Performance
- Capacitor vs Capacitance
- Getting Answers to Your LDO Questions ASAP





Texas Instruments

Quick LDO Architecture Refresher





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- Noise
- PSRR
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Where Does Noise Come From?

- Total LDO output voltage noise is composed of **Input** \bullet **noise** that is coupled to the output, as well as **intrinsic noise** generated by the LDO.
 - **Power Supply Rejection Ratio** (PSRR) measures • how much noise from the input couples into the output through the pass device.
 - **Intrinsic noise** is dominated by the noise of the ulletinternal reference and error amplifier.





 V_{IN}

 $1/R_{O}$



Bandgap Filter Using Noise Reduction (NR) Pin Ex: TPS7A83A, TPS7A47

The Reference Voltage noise can be filtered with an RC filter. This can be external or internal. On external devices, add a capacitor to the NR pin.







Increasing C_{NR} pushes noise lower.

Feed Forward Cap Reduces AC-Gain



- Error amp regulates so that Vfb=Vref, so any noise on Vref will also be present on Vfb.
 - $V_{out} = V_{ref} * \frac{R_1 + R_2}{R_2}$
 - Any noise on Vref is gained up!
- C_{FF} acts as a short at higher frequencies which reduces the closed-loop gain reducing the amplification at higher . frequencies
- With a C_{FF} , noise should be similar to values in unity gain configuration.
- App note on the pros and cons of using a Cff http://www.ti.com/lit/an/sbva042/sbva042.pdf



1k





 V_{IN} = 2.2 V, V_{OUT} = 1.2 V, I_{OUT} = 1.0 A, C_{IN} = C_{OUT} = 10 μ F, C_{NR/SS} = 10 nF, V_{RMS} BW = 10 Hz to 100 kHz

What Conditions Effect Noise

Number one thing that effects noise performance is the output voltage

The next thing that effects noise is the noise reduction capacitor







And the final thing that effects noise to a large degree is the feedforward capacitor

Figure 10. Spectral Noise Density vs Frequency and C_{FF}

What Conditions Do Not Effect Noise

Number one thing that has almost no effect on noise is output current

The next thing that has very little effect on noise is Vin









The final thing is output capacitor (very large Cout can show some difference)

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TEXAS INSTRUMENTS

PSRR

PSRR (Power Supply Rejection Ratio) represents the ability of the LDO to filter input voltage changes. This is critical for low-noise applications.







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The Importance of LDO PSRR

- DC/DC (switching) converters are necessary for efficiency, however • they are very noisy
 - Many devices are very sensitive to power supply noise
 - DC/DC converters are commonly followed by an LDO to clean the supply







TEXAS INSTRUMENTS

Typical PSRR Curve

Region 1 is determined by:

- PSRR of the Reference and the effectiveness of the RC filter Region 2 is determined by:
- Open-Loop Gain of Error Amplifier

Region 3 is determined by:

- Parasitic capacitance of the FET and the output capacitor (capacitive divider)
 - The smaller the parasitic cap the less the Vin is AC coupled to Vout
 - The larger Cout the more noise is shunted to GND









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What Conditions Effect PSRR







What Conditions Do Not Effect PSRR

Number one thing that has The next thing that only almost no effect on PSRR is has a small effect on Vbias>min **PSRR** is Vout 100 V_{OUT} = 0.8 V $V_{BIAS} = 3.0 V$ Power-Supply Rejection Ratio (dB) $V_{OUT} = 0.9 V$ Ratio (dB) $V_{BIAS} = 5.0 V$ V_{OUT} = 1.1 V $V_{BIAS} = 6.5 V$ 80 80 $V_{OUT} = 1.2 V$ V_{OUT} = 1.5 V V_{OUT} = 1.8 V Supply Rejection 60 60 V_{OUT} = 2.5 V 40 -Jower-2020 100k 100 1M 10M 10 10k 10 100 10k 100k 1M 10M 1k

Figure 3. PSRR vs Frequency and V_{BIAS}

Frequency (Hz)

100

100

80

60

40

20

10

(qB)

Ratio

Rejection

Supply

Power-

Frequency (Hz)

Figure 5. PSRR vs Frequency and V_{OUT} With Bias





The final thing that has some effect (but only at high freq) is output capacitor



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TEXAS INSTRUMENTS

JEDEC Thermals

- Because an IC's thermal dissipation is subject to many variables we use the JEDEC standard (JESD51) for all thermal modeling.
- The JEDEC standard is used so that devices can be easily compared on a similar basis.
 - if a competitor is not reporting the JEDEC standard the customer should consider why they don't want to be directly compared to other devices.
- Common thermal metrics: θ_{JA} , θ_{JB} , $\theta_{JC(top)}$, $\theta_{JC(bot)}$ **TI Datasheet**

Competitor Datasheet

			TPS732 ⁽³⁾					
	THERMAL METRIC ⁽¹⁾⁽²⁾	DRB [SON]	DCQ [SOT223]	DBV [SOT23]	UNIT			
		8 PINS	6 PINS	5 PINS				
R _{eja}	Junction-to-ambient thermal resistance	58.3	53.1	205.9				
R _{€JC(top)}	Junction-to-case (top) thermal resistance	93.8	35.2	119				
R _{ejb}	Junction-to-board thermal resistance	72.8	7.8	35.4	°C 11			
₽јт	Junction-to-top characterization parameter	2.7	2.9	12.7	C/VV			
₽јв	Junction-to-board characterization parameter	25	7.7	34.5				
R _{0JC(bot)}	Junction-to-case (bottom) thermal resistance	5	N/A	N/A				
1) For m 2) For th 3) Therm specifi	ore information about traditional and new thermal metrics, s ermal estimates of this device based on PCB copper area, s al data for the DRB, DCQ, and DRV packages are derived ied in the JESD51 series. The following assumptions are us	ee the <i>IC Package Therr</i> see the <i>TI PCB Thermal</i> by thermal simulations b ed in the simulations:	nal Metrics appli Calculator. ased on JEDEC	cation report, SPR -standard methodo	A953. Dogy as			

i.	DRB:	The	exposed	pad	is	connected	to	the	PCB	ground	layer	through	а	2	×	2	thermal	via	array.
ii.	DCQ:	The	exposed	pad	is	connected	to	the	PCB	ground	layer	through	а	3	x	2	thermal	via	array.

THERMAL CHARACTERISTICS						
Characteristic	Te	est Conditions	(Typical Value)	Unit		
DPAK 5-PIN PACKAGE						
	Min Pad Board (N	lote 3)	1" Pad Board (Note 4)			
Junction–to–Tab (psi–JLx, ψ_{JLx})	4.2		4.7	C/W		
Junction-to-Ambient (R _{BJA} , θ _{JA})		46.8	C/W			
D ² PAK 5-PIN PACKAGE						
	0.4 sq. in. Spreader Bo	ard (Note 5)	1.2 sq. in. Spreader Board (Note 6)			
Junction–to–Tab (psi–JLx, ψ_{JLx})	3.8		4.0	C/W		
Junction-to-Ambient (R _{θJA} , θ _{JA})	74.8		41.6	C/W		
 1 oz. copper, 0.26 inch² (168 mm²) copper 1 oz. copper, 1.14 inch² (736 mm²) copper 1 oz. copper, 0.373 inch² (241 mm²) copper 1 oz. copper, 1.222 inch² (788 mm²) copper 	area, 0.062" thick FR4. area, 0.062" thick FR4. r area, 0.062" thick FR4. r area, 0.062" thick FR4.	28mr top s	n x 28mm area of side dedicated to	n the only		



thermal dissipation?

θ_{JA}: Understanding Usage and Limitations

• The junction-to-ambient thermal resistance, θ_{JA} , is the most commonly used thermal metric.

 $-\theta_{IA}$ is a measure of the thermal performance of an IC mounted on a PCB.

- θ_{IA} is used since the ambient temperature is one of the few temperatures that designers have accurate data on. $T_I = T_A + (\theta_{IA} * P_D)$
 - The board acts as the main heat sink for any IC attached to it
 - If the actual application board is significantly different from the JEDEC High-K board this can result in an estimate that is unrealistic

Factors Affecting θja	Strength of Influence (rule of thumb)	Relation to θja
PCB design	Very Strong	The more metal connected to the IC the lower θ a due to
Chip or pad size	Strong	The larger the chip and thermal pad the lower θ a due
Altitude	Medum	The lower the altitude the lower θ and the increased co
External ambient temperature	Weak	The higher the ambient temp the lower θja due to incre transfer
Power dissipation	Very Weak	The higher the junction temp the lower θ a due to incr





o larger thermal mass e to heat spreading oling efficiency of air eased radiative heat

reased heat transfer

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JEDEC High-K Board

- TI LDO thermal metrics are modeled using the JEDEC High-K Board (2s2p)
- The JEDEC High-K board has:
 - Two internal layers which have ~5500mm² of 1oz copper (1 GND & 1 PWR plane)
 - Bottom layer (opposite the IC) thermal relief layer which has ~1100mm² of 2oz copper
 - Internal GND plane and bottom GND plane are connected to the thermal pad using as many thermal vias as can be fit within the power pad dimensions.
 - The top layer only has traces running straight to the pins.
- The JEDEC high-k board is good but not 100% optimized for maximum thermal dissipation











R plane) f 2oz copper ad using as many

JEDEC HIGH-K 2s2p	JEDEC LOW-K 1s0p			
0.00	28 in			
0.98 in				
0.062 in				
4	in			
4.5	5 in			
0.0014in (2 planes)	No internal copper planes			

Guidelines For Maximum Thermal Relief

✓ Have as much metal as possible in the areas around the device (both on the same layer and the layers below it)

- 2oz copper is better than 1oz copper simply because there is extra metal
- The more thermal vias the better spreading the heat between the different layers
- ✓ The largest array of thermal vias in the thermal pad maximizes the amount of heat which can be transferred from the LDO to the internal and bottom layers.
 - A 6x6 array allows the internal layers to dissipate heat almost as well as the top layer which is often crowded with other components.
 - Vias should be as small as possible to decrease the amount of open space in the via hole (this maximizes the amount of metal)
 - If the power pad is too small to put many vias in, then placing extra vias as close as possible to the power pad is still helpful
- If the board is large, there is a lot of metal, and the thermal vias are maximized then it is possible to reduce the θja by 25-50%.

2s2p







JEDEC

1s0p





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Other Thermal Considerations

- Nearby heat sources on the PCB can reduce the ability of the LDO to shed heat to the board
 - This is because those other heat sources increase the local board temperature decreasing the temperature differential between the board to the LDO in question
- Load pulses can still heat the die significantly if the duty cycle isn't low
 - A step increase in power dissipation will cause the die temp to stabilize on the order of hundreds of milliseconds to 1 second
 - For ~1 second pulses the LDO should reach a similar internal temp as if the load was on constantly
 - Pulses of tens of milliseconds don't heat the die nearly as much
- Forced convection and board level heatsinks can help significantly, though they are rarely a consideration for many applications which have to rely on passive cooling only
 - The thermal models in our datasheets assume natural convection (no forced air).





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- Most of TI's commercial LDOs are designed such that they can be qualified to the Q100 Grade 1 standards
- There can be challenges when taking some of our LDOs through the Grade 0 qualification.
 - Package: Leaded vs Leadless packages
 - Materials used: IC's top level metal and bond wire materials must be chosen appropriately
- Due to complexity of designing for Grade 0 it is best to design and plan for Grade 0 qualification at the beginning of a new design







ACCELERATED ENVIRONMENT STRESS TESTS

ADDITIONAL REQUIREMENTS

PC before TC for surface mount devices. Grade 0: -55°C to +150°C for 2000 cycles or equivalent. Grade 1: -55°C to +150°C for 1000 cycles or equivalent.

PC before PTC for surface mount devices. Test required only on devices with maximum rated power \geq 1 watt or $\Delta T_{J} \geq$ 40°C or devices designed to drive inductive loads. Grade 0: T_a of -40°C to +150°C for 1000 cycles.

Grade 1: Ta of -40°C to +125°C for 1000 cycles.

Grade 0: +175°C T_a for 1000 hours or +150°C T_a for Grade 1: +150°C T_a for 1000 hours or +175°C T_a for 500

ACCELERATED LIFETIME SIMULATION TESTS

ADDITIONAL REQUIREMENTS

For devices containing NVM, endurance preconditioning must be performed before HTOL per Q100-005.

Grade 0: +150°C T_a for 1000 hours.

Grade 1: +125°C T_a for 1000 hours.

Grade 2: +105°C T_a for 1000 hours.

Grade 3: +85°C Ta for 1000 hours.

If Ti is used to set the HTOL conditions, the minimum stress of 1000 hours at the Ta of the device is to be shown using activation energy of 0.7ev or other value technically justified.

- TC and PTC: Leadless packages struggle to pass Grade 0 standards due to the different coefficients of thermal expansion (CTE) of the IC and the PCB.
 - Solder joints often break due to different rates of expansion
 - The CTE changes significantly when you surpass the glass transition temperature (Tg) ~130C-160C
 - The metal leads on leaded packages can move as the IC and PCB expand at differing rates which puts less stress on the solder attaching the IC to the PCB.

	ACCELERATED ENVIRO						
	STRESS						
	Temperature Cycling	PC before TC Grade 0: - Grade 1: -					
	Power Temperature Cycling	PC before P only on device 40°C or device Grade 0: 1 Grade 1: 1					
	High Temperature Storage Life	gh Temperature orage Life Plastic Pack Grade 0: 2000 hour Grade 1: hours.					
	ACCELERATED LIFETI						
	STRESS						
	High Temperature Operating Life	For devices must be per Grade 0: Grade 1: Grade 2: Grade 2: HTOL NOTE If Ti is us stress of shown u technica					





DNMENT STRESS TESTS

ADDITIONAL REQUIREMENTS

for surface mount devices. <u>-55°C</u> to +150°C for 2000 cycles or equivalent. <u>-55°C</u> to +150°C for 1000 cycles or equivalent.

PTC for surface mount devices. Test required es with maximum rated power ≥ 1 watt or $\Delta T_J \ge$ es designed to drive inductive loads. T_a of -40°C to +150°C for 1000 cycles. T_a of -40°C to +125°C for 1000 cycles.

aged Parts

+175°C T_a for 1000 hours or +150°C T_a for s. +150°C T_a for 1000 hours or +175°C T_a for 500

ME SIMULATION TESTS

ADDITIONAL REQUIREMENTS

s containing NVM, endurance preconditioning rformed before HTOL per Q100-005.

+150°C Ta for 1000 hours.

: +125°C Ta for 1000 hours.

: +105°C T_a for 1000 hours.

: +85°C Ta for 1000 hours.

ES:

used to set the HTOL conditions, the minimum of 1000 hours at the Ta of the device is to be using activation energy of 0.7ev or other value ally justified.

- HTSL: Chemical interactions that take place between bond wires and metal layers are sped up due to increased temperature which can cause failures
 - HTSL usually causes Kirkendall Voiding failures
 - Kirkendall Voiding is caused by the diffusion of one metal into another metal. This chemical reaction increases as the temperatures increases.



To reduce the likelihood of failure at the increased temperatures Grade
 0 qualification requires the selection of the proper materials

ACCELERATED ENVIRO						
STRESS						
Temperature Cycling	PC before TC Grade 0: - Grade 1: -					
Power Temperature Cycling	PC before P only on device 40°C or device Grade 0: 1 Grade 1: 1					
High Temperature Storage Life	Plastic Packa Grade 0: 2000 hours Grade 1: hours.					
ACCELERAT	ACCELERATED LIFETI					
STRESS						
High Temperature Operating Life	For devices must be per Grade 0: Grade 1: Grade 2: Grade 3: <u>HTOL NOTE</u> If Tj is us stress of shown u technica					





DNMENT STRESS TESTS

ADDITIONAL REQUIREMENTS

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PTC for surface mount devices. Test required es with maximum rated power ≥ 1 watt or ΔT_J ≥ es designed to drive inductive loads. T_a of -40°C to +150°C for 1000 cycles. T_a of -40°C to +125°C for 1000 cycles.

aged Parts

+175°C $\underline{T_a}$ for 1000 hours or +150°C $\underline{T_a}$ for s. +150°C $\underline{T_a}$ for 1000 hours or +175°C $\underline{T_a}$ for 500

IME SIMULATION TESTS

ADDITIONAL REQUIREMENTS

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: +150°C Ta for 1000 hours.

: +125°C Ta for 1000 hours.

: +105ºC Ta for 1000 hours.

: +85°C T_a for 1000 hours.

ES:

used to set the HTOL conditions, the minimum of 1000 hours at the Ta of the device is to be using activation energy of 0.7ev or other value ally justified.

- HTOL: physical interactions that take place in bond wires and metal layers are sped up due to increased temperature which can cause failures
 - HTOL usually causes Electromigration failures
 - Electromigration is the physical movement of metal atoms caused by electrons running into those metal atoms. The higher the temperature the more collisions there are, eventually causing an open circuit due to missing metal atoms



To reduce the likelihood of failure at the increased temperatures Grade
 0 qualification requires the selection of the proper materials

ACCELERATED ENVIRO				
STRESS				
Temperature Cycling	PC before TC f Grade 0: - <u>-</u> Grade 1: - <u>-</u>			
Power Temperature Cycling	PC before PT only on device 40°C or device Grade 0: T Grade 1: T Plastic Packag Grade 0: 2000 hours Grade 1: 4 hours.			
High Temperature Storage Life				
ACCELERAT	ED LIFETI			
STRESS				
High Temperature Operating Life	For devices must be perf Grade 0: Grade 1: Grade 2: Grade 3: <u>HTOL NOTE</u> If Tj is us <u>stress of</u> <u>shown us</u> technical			





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: +85°C Ta for 1000 hours.

ES:

used to set the HTOL conditions, the minimum of 1000 hours at the Ta of the device is to be using activation energy of 0.7ev or other value ally justified.

HTOL Grade 1 vs Grade 0

- Mission Profiles
 - We can use mission profiles which have temperature (ambient or board) and power dissipation profiles to calculate how it compares with the AEC-Q100 HTOL profile.
- Grade 1 vs Grade 0
 - Grade 1 assumes average Tj=~55C for approximately 9 years
 - Grade 0 assumes average Tj=~70C for approximately 9 years

Device Name:	TLV702-Q	2-Q Arrhenius calculations							
Package	DBV	units							
EA	0.7	ev	$E_{a}\left(\frac{1}{\pi^{1}}-\frac{1}{\pi^{2}}\right)$						
K	8.63E-05	constant							
Power	0.2618	W	$-\frac{2\omega}{k}(T1 T2)$						
θjb	69.3	C/W	AF	$\equiv e^{\kappa}$					
Delta C	18.14274	С							
Oven Stress Temp	150	С	O	range cells c	an be chai	nged.			
				_					
T _b Customer Requirments	T _j Customer Requirments	Hrs Customer Requirements	T _{oven} C HTOL	Hrs HTOL Conditions	AF	°K (T1)	°K (T2)		
-40	-21.86	316.00	150	0.0	503545.09	251.14	423		
-20	-1.86	316.00	150	0.0	46431.60	271.14	423		
23	41.14	0.00	150	0.0	//1.69	314.14	423		
30	48.14	0.00	150	0.0	439.42	321.14	423		
40	56.14	3.00	150	0.0	204.00	24114	423		
50	68.14 79.14	276.00	150	2.8	99.87 50.72	341.14	423		
70	78.14 88.14	1196.00	150	44.7	26.74	361 14	423		
80	98.14	3268.00	150	223.9	14.60	371 14	423		
90	108 14	2493.00	150	3031	822	38114	423		
100	118.14	1385.00	150	290.3	4.77	391.14	423		
110	128.14	576.00	150	202,5	2.84	401.14	423		
125	143.14	105.00	150	76.5	1.37	416.14	423		
Total hours needed for Mu	Itiple T-=Hr require	ments		1155.6					





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TEXAS INSTRUMENTS

Capacitor & Capacitance Defined

- Capacitor: a device used to store an electric charge, consisting of one or more pairs of conductors separated by an insulator.
- Capacitance: the ability to store an electric charge.
- In an Ideal world the value written on a capacitor would be exactly the same as the amount of capacitance it provides when inserted into a system.
 - (Un)Fortunately we do not live in a world with ideal components • The existence of an ideal components would leave me without a job!





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Capacitor vs Capacitance Explained

- There are three main reasons why the capacitance of a capacitor isn't always what it says on the label
- 1. Derating due to being biased with a DC Voltage
- 2. Derating due to changes in temperature
- 3. Manufacturing tolerances
 - This is called out specifically in the specs and is usually $\pm 10\%$ or $\pm 20\%$ ____





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DC Voltage Derating Explained

- When a DC Voltage is applied to a capacitor it creates an E-field which "locks" some of the atomic dipoles into place.
 - These "locked" dipoles do not react to AC voltage transients which is why the effective capacitance decreases.





5V





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Capacitance vs DC Bias

Capacitance vs DC Bias vs Cap Size

Murata: 10uF, 10V, X5R, 0.95mm, +-20%

Key Take Away

The same voltage applied across a thicker dielectric results in a lower E-Field which will "lock in" less dipoles and cause less derating







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Capacitance vs Temperature Decoder Ring

Like all electronics capacitors have a temperature rating over which their performance is specified

Majority of LDO junction temperatures are usually specified from -40C to 125C.

1st Character: Low Temp		2nd Character: High Temp		3rd Character: Max Change over Temp	
Char	Temp (°C)	Char	Temp (°C)	Char	Change (%)
Z	10	2	45	А	±1.0
Y	-30	4	65	В	±1.5
Х	-55	5	85	С	±2.2
		6	105	D	±3.3
		7	125	Е	±4.7
		8	150	F	±7.5
		9	200	Р	±10
				R	±15
				S	±22
				Т	+22, -33
				U	+22, -56
				V	+22, -82





So we usually recommend X5R or X7R caps

TEXAS INSTRUMENTS

Capacitance vs Temperature Graph

Capacitance vs Temp vs Temp Rating Murata: 10uF, 10V, 0805, +-20% 12 10 8 Capacitance[uF] 6 4 2 -55 20 -40 -25 -10 5 35 50 65 80

Temnp [C]

Temperature affects the capacitance much less than the DC Bias which can reduce the capacitance by 90%





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Fastest Way to Get Answers

- The fastest way to get an answer to a question regarding LDOs is to post it on <u>E2E</u>
 - We know many people think that sending an email directly to one of the Apps Engineers (or better yet the Apps Manager!) will get them the fastest response.
 - However, this is **not** effective because like you each day we come in to inboxes full of emails which we must dig through to find the customer questions.
 - Instead we prioritize questions posted on E2E

Starting around Q4 of last year we started informing the field that E2E was the most effective way of submitting questions and as you can see it's working with E2E threads going up by almost 20%



E2E Questions Posted per Quarter



Why Use E2E?

- It's faster because we have multiple people dedicated to monitoring and responding to all of the questions that are posted on E2E.
- Posting on E2E allows us to effectively track customer support metrics which can help us to justify dedicating even more resources to customer support.
 - -Email has no effective way of tracking customer support metrics
- Posting on E2E also enables anybody to easily search for the answers to similar questions.
 - -An email in another person's inbox isn't searchable by any one else on the team





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Questions with Customer IP

- We understand that some customers may have sensitive IP in their questions and those should not go on E2E, please send those requests to your field rep or **myself** and I'll see that they are handled appropriately.
 - Examples of Customer IP include schematics or board layouts









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Troubleshooting Questions

- If you are working through an issue and need our help please provide as many of the following as possible
- In order of importance
- 1. Scope Shots
 - Scope shots are the best way for us to evaluate what is happening without being with the customer
 - They should include Vin, Ven, Vout and lout if possible
 - If Vbias present or if PG is part of the issue include these ٠

- 2. Schematics
- Input and output conditions 3.
 - Vin, Vout (nominal), Cin, Cout, Cnr, Cff, lout (is the load constant or changing?), what is driving Ven?
- 4. Board Layout
 - Not always needed immediately unless the problem seems related to: thermals, EMI, or PSRR/noise that is worse than expected





With these two items we can debug ~75% of issues remotely

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